

# DIONICS INC.

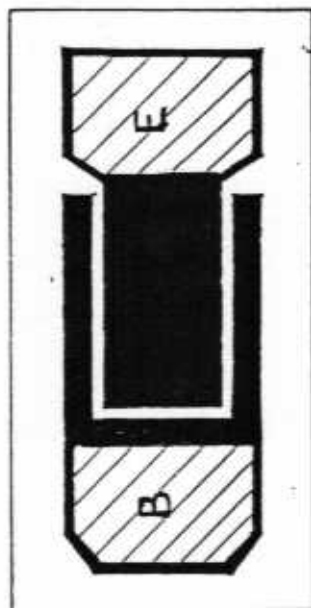
65 RUSHMORE ST., WESTBURY, N.Y. 11590 516-997-7474

## SPECIFICATION SHEET

TYPE: 2N3906  
PNP

CHIP APPEARANCE

CHIP SIZE: 10.0 x 18.0 mils



CHIP THICKNESS: 7.0<sup>+1.0</sup> mils

BONDING PAD DIMENSIONS in MILS

BASE: 3.0 x 4.5

EMITTER: 3.0 x 4.5

METALLIZATION:

TOP: ALUMINUM

BACKSIDE: GOLD / Si

WAFER DIAMETER: 3-INCH

NOTES:

ABSOLUTE MAXIMUM RATINGS:

ITEM	SYMBOL	RATINGS	UNIT
COLLECTOR-BASE VOLTAGE	V CBO	-40	V
COLLECTOR-EMITTER VOLTAGE	V CEO	-40	V
EMITTER-BASE VOLTAGE	V EBO	-5	V
COLLECTOR CURRENT	I C	-200	mA
COLLECTOR LOSS	P C	300	mW
JUNCTION TEMPERATURE	T j	150	deg-C
STORAGE TEMPERATURE	T <sub>stg</sub>	-55/+150	deg-C

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ITEM	SYMBOL	COND.	MIN.	Typ.	MAX.	UNIT
COLLECTOR-EMITTER BREAKDOWN VOLTAGE	BV CEO	IC= 1mA	-40	-	-	V
COLLECTOR-BASE BREAKDOWN VOLTAGE	BV CBO	IC= 10uA	-40	-	-	V
EMITTER-BASE BREAKDOWN VOLTAGE	BV EBO	IE= 10uA	-5	-	-	V
COLLECTOR SATURATION	VCE (SAT)	IC= 50mA IB= 5mA	-	-	-0.4	V
DC CURRENT GAIN	H FE	VCE= 1V IC= 10mA	100	-	-	
TRANSITION FREQUENCY	ft	VCE= 20V IC= 10mA	250	-	-	MHz
OUTPUT CAPACITANCE	COB	VCB= 5V f= 100KHz	-	-	4.5	pF

## PROBING SPEC:

NO.	MODE	LIMIT		CONDITION
		MIN.	MAX.	
1	V BE	-	-0.9V	IB= -10mA
2	BV CEO	-44V	-	IC= -0.1mA
3	I CBO	-	-0.3uA	VCB= -42V
4	I EBO	-	-1uA	VEB= -5.5V
5	I CEO	-	-1uA	VCE= -42V
6	H FE	120	270	VCE= -1V IC= -10mA
7	VCE (SAT)	-	-0.3V	IC= -50mA IB= -5mA

